

HAILS, J. et al.
Serial No. unknown

REMARKS

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page(s) is captioned "Version With Markings To Show Changes Made."

Respectfully submitted,

NIXON & VANDERHYE P.C.

By: _____


Arthur R. Crawford
Reg. No. 25,327

ARC:ecb
1100 North Glebe Road, 8th Floor
Arlington, VA 22201-4714
Telephone: (703) 816-4000
Facsimile: (703) 816-4100

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION

Page 1, before the first line, please insert as a separate paragraph:

This application is the US national phase of international application

PCT/GB00/03249 filed 22 August 2000, which designated the US.

IN THE CLAIMS

11. A method of fabricating an electronic device comprising the steps of (a) depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ onto a substrate by a method according to ~~any one of~~ Claims 1 to 10; and (b) connecting at least two electrodes to the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$.

14. A method of fabricating a device according to ~~one of~~ Claims 11 or 12 wherein the method further comprises the step of growing a passivating layer of CdTe on the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$.

15. A device obtainable by a method according to ~~one of~~ Claims 11 to 14.

16. An infrared detector comprising an array of devices, each device being obtainable by a method according to ~~one of~~ Claims 11 to 14.

17. $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ obtainable by a method according to ~~one of~~ Claims 1 to 10.